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FDS3590

80V N-Channel PowerTrench® MOSFET

General Description

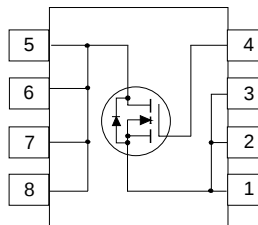
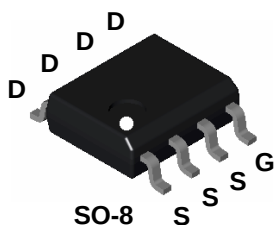
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

These MOSFETs feature faster switching and lower gate charge than other MOSFETs with comparable $R_{DS(ON)}$ specifications.

The result is a MOSFET that is easy and safer to drive (even at very high frequencies), and DC/DC power supply designs with higher overall efficiency.

Features

- 6.5 A, 80 V $R_{DS(ON)} = 39\text{ m}\Omega$ @ $V_{GS} = 10\text{ V}$
 $R_{DS(ON)} = 44\text{ m}\Omega$ @ $V_{GS} = 6\text{ V}$
- Low gate charge
- Fast switching speed
- High performance trench technology for extremely low $R_{DS(ON)}$
- High power and current handling capability



Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain-Source Voltage	80	V
V_{GSS}	Gate-Source Voltage	± 20	V
I_D	Drain Current – Continuous (Note 1a)	6.5	A
	– Pulsed	50	
P_D	Power Dissipation for Single Operation (Note 1a) (Note 1b) (Note 1c)	2.5	W
		1.2	
		1.0	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	50	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	25	$^\circ\text{C/W}$

Package Marking and Ordering Information

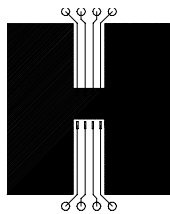
Device Marking	Device	Reel Size	Tape width	Quantity
FDS3590	FDS3590	13"	12mm	2500 units

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

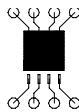
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Drain-Source Avalanche Ratings (Note 2)						
W _{DSS}	Single Pulse Drain-Source Avalanche Energy	V _{DD} = 40 V, I _D = 6.5 A			175	mJ
I _{AR}	Maximum Drain-Source Avalanche Current				6.5	A
Off Characteristics						
BV _{DSS}	Drain–Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	80			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		88		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 64 V, V _{GS} = 0 V			1	μA
I _{GSSF}	Gate–Body Leakage, Forward	V _{GS} = 20 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate–Body Leakage, Reverse	V _{GS} = –20 V, V _{DS} = 0 V			–100	nA
On Characteristics (Note 2)						
V _{GS(th)n}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	2		4	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		–6		mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	V _{GS} = 10 V, I _D = 6.5 A V _{GS} = 10 V, I _D = 6.5 A, T _J = 125°C V _{GS} = 6 V, I _D = 4.5 A		32 61 34	39 86 44	mΩ
I _{D(on)}	On–State Drain Current	V _{GS} = 10 V, V _{DS} = 5 V	25			A
G _{FS}	Forward Transconductance	V _{GS} = 10 V, I _D = 6.5 A		25		S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 40 V, V _{GS} = 0 V, f = 1.0 MHz		1180		pF
C _{oss}	Output Capacitance			171		pF
C _{rss}	Reverse Transfer Capacitance			50		pF
Switching Characteristics (Note 2)						
t _{d(on)}	Turn–On Delay Time	V _{DD} = 40 V, I _D = 1 A, V _{GS} = 10 V, R _{GEN} = 6 Ω		11	20	ns
t _r	Turn–On Rise Time			8	16	ns
t _{d(off)}	Turn–Off Delay Time			26	50	ns
t _f	Turn–Off Fall Time			12	25	ns
Q _g	Total Gate Charge	V _{DS} = 40 V, I _D = 6.5 A, V _{GS} = 10 V		25	35	nC
Q _{gs}	Gate–Source Charge			4.5		nC
Q _{gd}	Gate–Drain Charge			5.8		nC
Drain–Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain–Source Diode Forward Current				2.1	A
V _{SD}	Drain–Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 2.1 A (Note 2)		0.74	1.2	V

Notes:

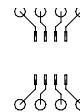
1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 50 $^\circ\text{C/W}$ when mounted on a 1in² pad of 2 oz copper



b) 105 $^\circ\text{C/W}$ when mounted on a 0.04 in² pad of 2 oz copper



c) 125 $^\circ\text{C/W}$ when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < 300 μ s, Duty Cycle < 2.0%

Typical Characteristics

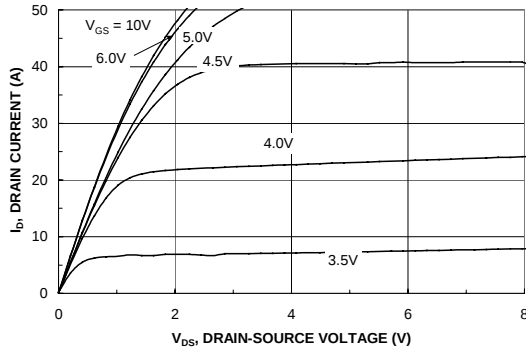


Figure 1. On-Region Characteristics.

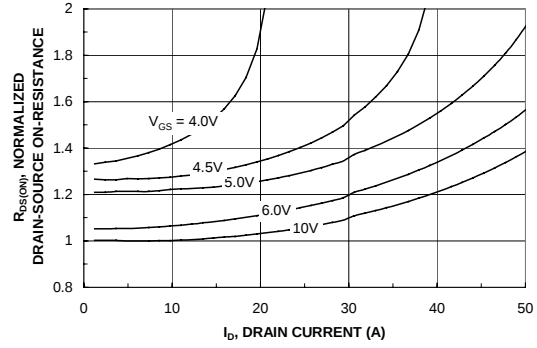


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

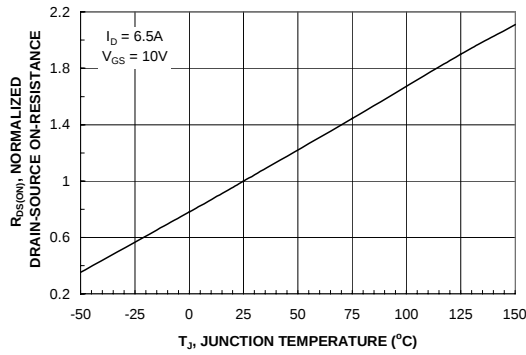


Figure 3. On-Resistance Variation with Temperature.

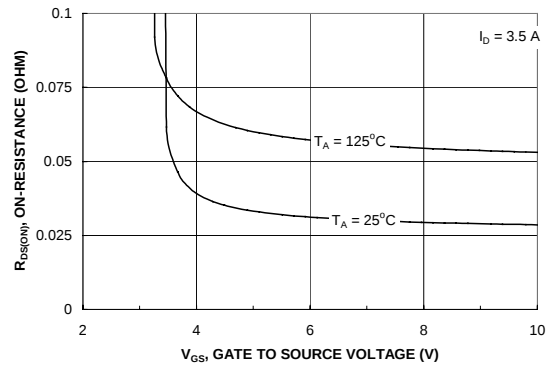


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

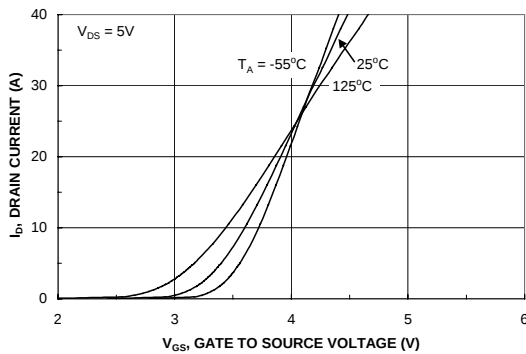


Figure 5. Transfer Characteristics.

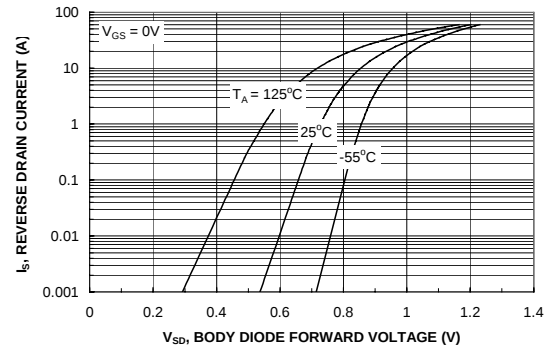


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

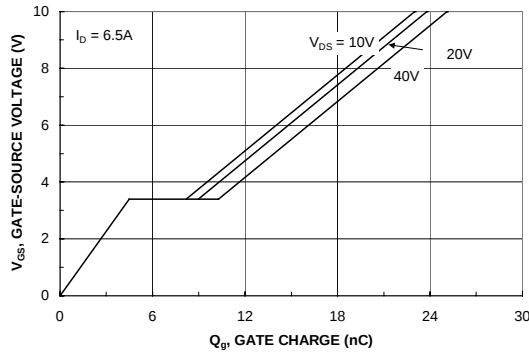


Figure 7. Gate Charge Characteristics.

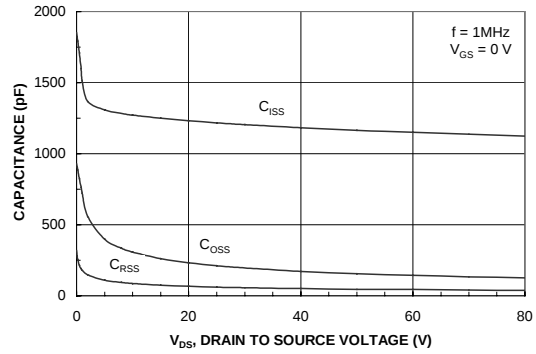


Figure 8. Capacitance Characteristics.

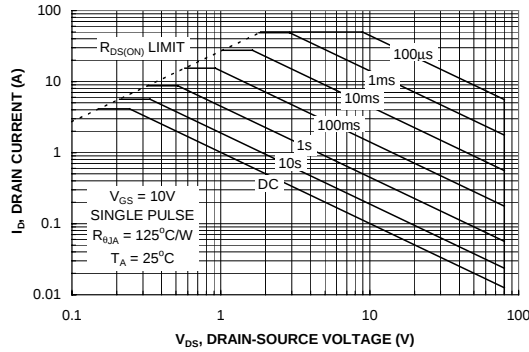


Figure 9. Maximum Safe Operating Area.

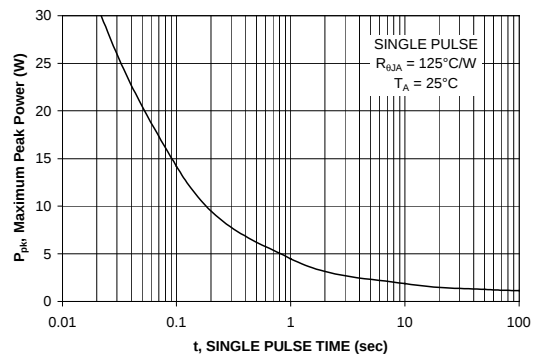


Figure 10. Single Pulse Maximum Power Dissipation.

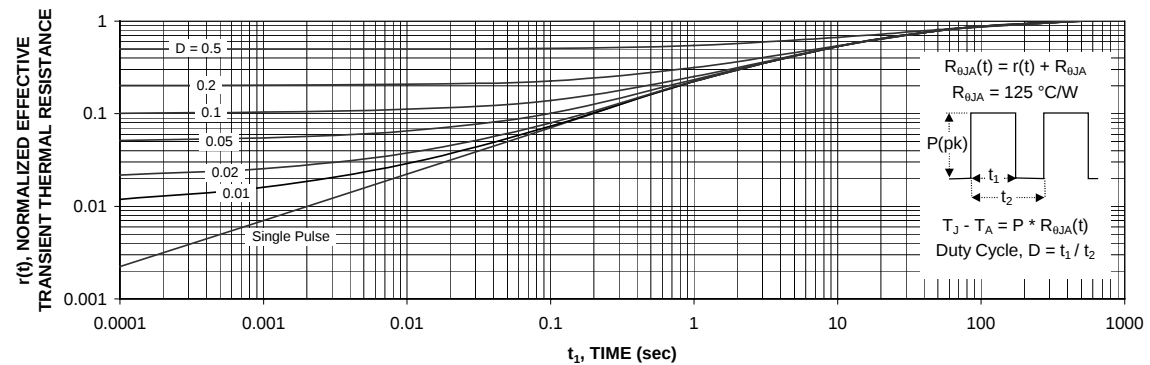


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c.
Transient thermal response will change depending on the circuit board design.

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